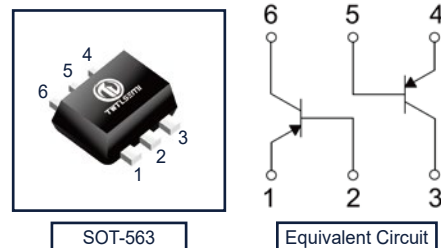


Features

- Epitaxial Die Construction
- Complementary NPN Types Available (BC847BV)
- Ultra-Small Surface Mount Package



MAXIMUM RATINGS (TA=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CE0}	Collector-Emitter Voltage	-45	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _c	Collector Current	-0.1	A
P _c	Collector Power Dissipation	0.15	W
R _{θJA}	Thermal Resistance from Junction to Ambient	833	°C/W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

Electrical Characteristics (TA=25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _c =-10μA, I _E =0	-50			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _c =-10mA, I _B =0	-45			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1μA, I _c =0	-5			V
I _{CBO}	Collector cut-off current	V _{CB} =-30V, I _E =0			-15	nA
h _{FE}	DC current gain	V _{CE} =-5V, I _c =-2mA	220		475	
V _{CE(sat)(1)}	Collector-emitter saturation voltage	I _c =-10mA, I _B =-0.5mA			-0.1	V
V _{CE(sat)(2)}		I _c =-100mA, I _B =-5mA			-0.4	V
V _{BE(sat)(1)}	Base-emitter saturation voltage	I _c =-10mA, I _B =-0.5mA		-0.7		V
V _{BE(sat)(2)}		I _c =-100mA, I _B =-5mA		-0.9		V
V _{BE(1)}	Base-emitter voltage	V _{CE} =-5V, I _c =-2mA	-0.6		-0.75	V
V _{BE(2)}		V _{CE} =-5V, I _c =-10mA			-0.82	V
f _T	Transition frequency	V _{CE} =-5V, I _c =-10mA, f=100MHz	100			MHz
C _{ob}	Collector output capacitance	V _{CB} =-10V, I _E =0, f=1MHz			4.5	pF
NF	Noise figure	V _{CE} =-5V, I _c =-0.2mA, f=1kHz, R _S =2KΩ, BW=200Hz			10	dB

Ordering information

Product ID	Pack	Naming rule	Marking	hFE(1)	Qty(PCS)
BC857BV	SOT-563	BC857BV ↓ 产品名称 product name	K5V	220-475	3000



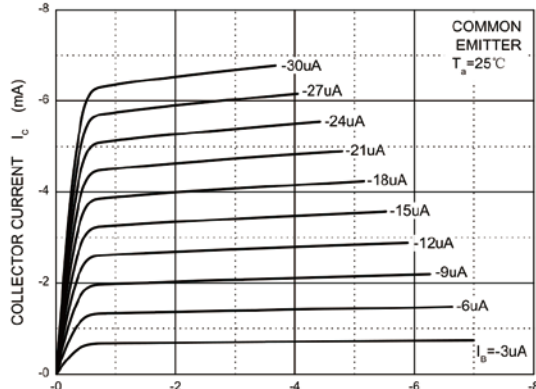
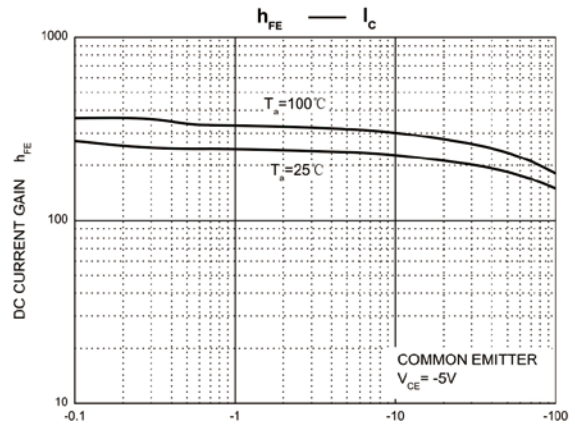
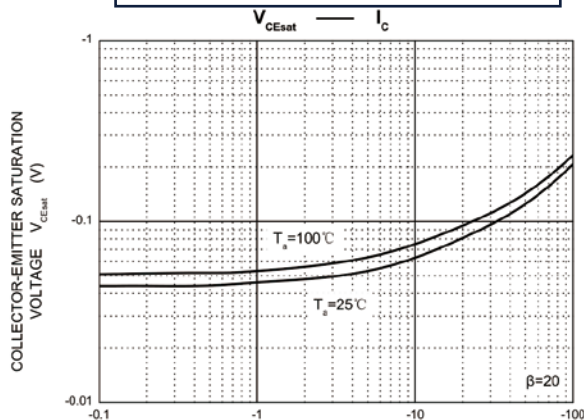
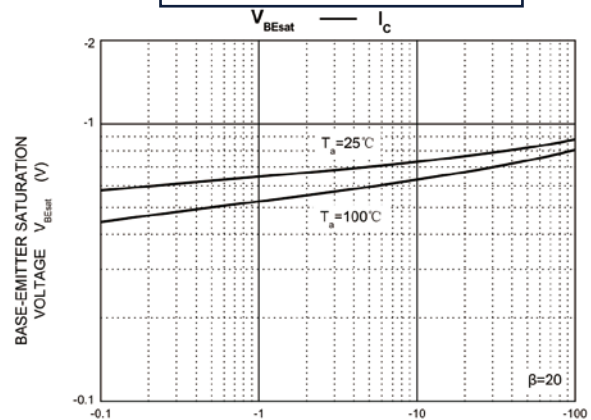
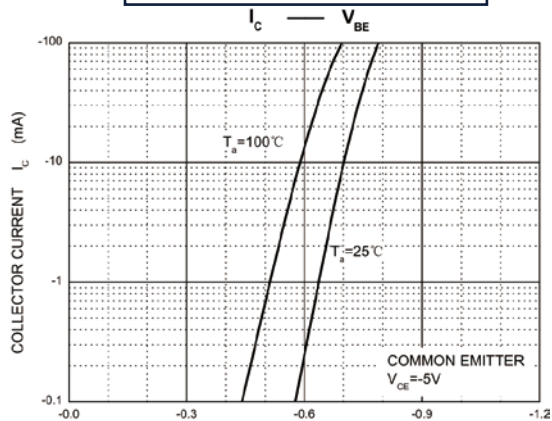
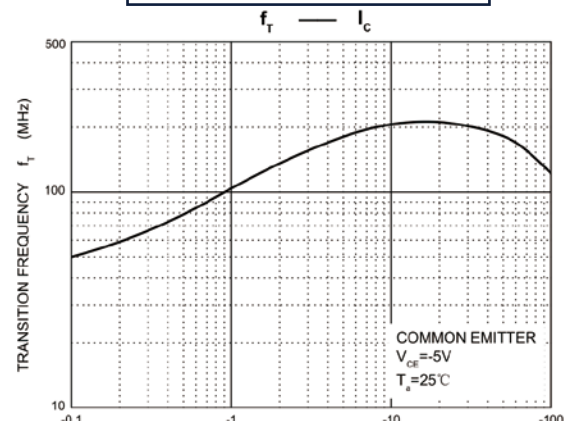
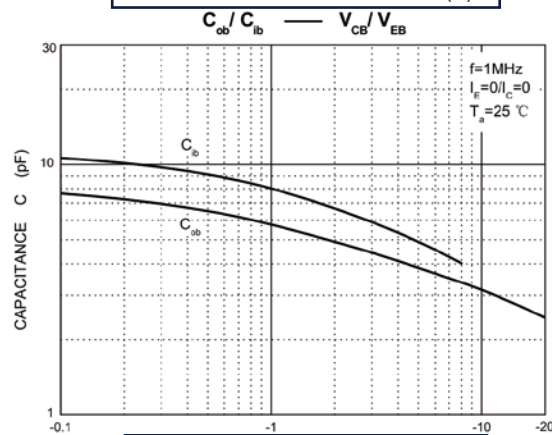
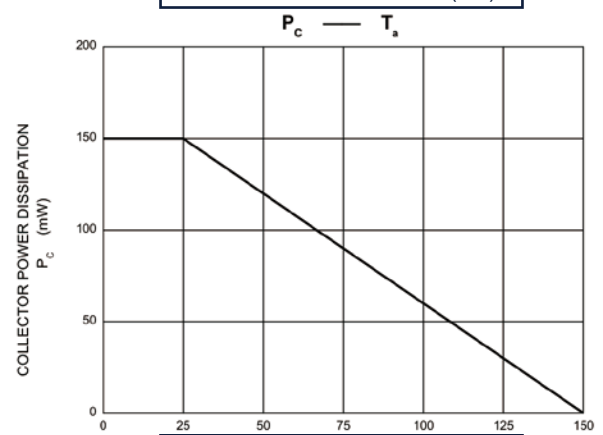
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SOT-563 DUAL TRANSISTOR (PNP+PNP)

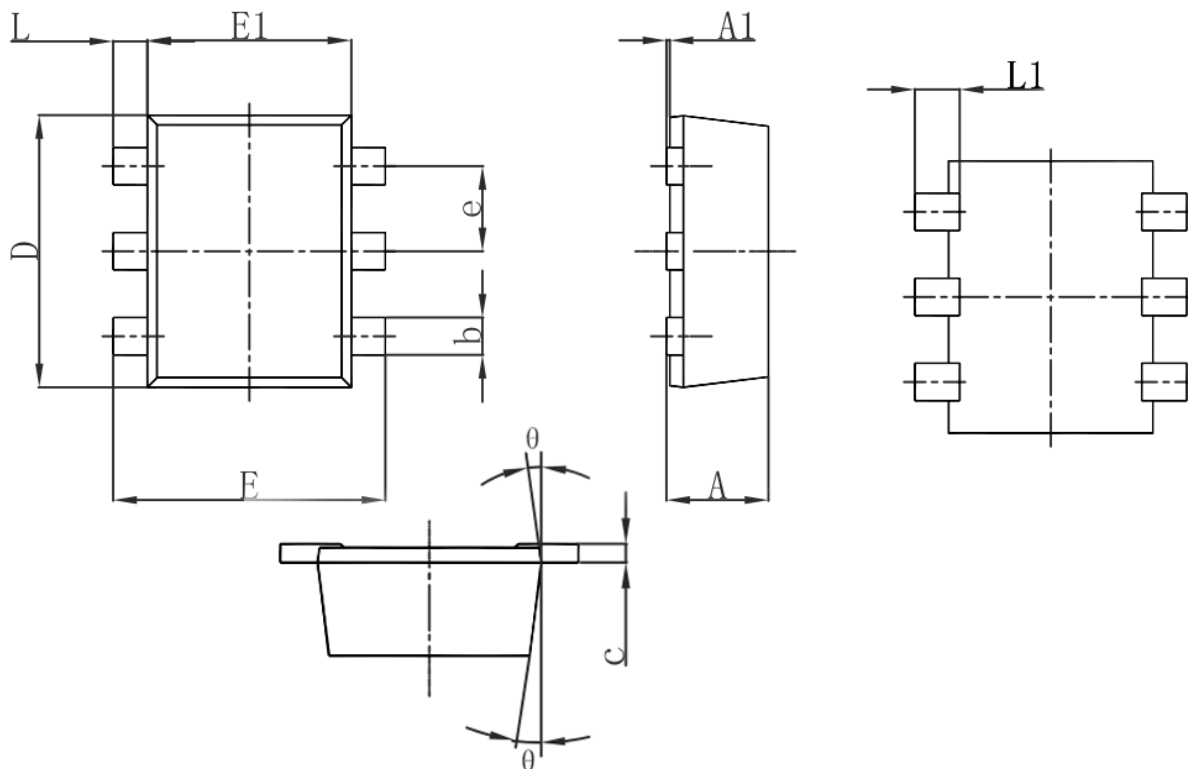
Typical Characteristics

Static Characteristic

COLLECTOR-EMITTER VOLTAGE $V_{CE}(V)$ COLLECTOR CURRENT $I_c(mA)$ COLLECTOR CURRENT $I_c(mA)$ COLLECTOR CURRENT $I_c(mA)$ BASE-EMITTER VOLTAGE $V_{BE}(V)$ COLLECTOR CURRENT $I_c(mA)$ REVERSE VOLTAGE $V_R(V)$ AMBIENT TEMPERATURE $T_a(^{\circ}\text{C})$



SOT-563 Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.06
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	10° REF.		10° REF.	